MC12080

1.1 GHz Prescaler

Description

The MC12080 is a single modulus divide by 10, 20, 40, 80 prescaler for low power frequency division of a 1.1 GHz high frequency input signal. Divide ratio control inputs SW1, SW2 and SW3 select the required divide ratio of ÷10, ÷20, ÷40, or ÷80.

An external load resistor is required to terminate the output. An 820 Ω resistor is recommended to achieve a 1.2 V_{pp} output swing, when dividing a 1.1 GHz input signal by the minimum divide by ratio of 10, assuming a 8.0 pF load. Output current can be minimized dependent on conditions such as output frequency, capacitive load being driven, and output voltage swing required. Typical values for load resistors are included in the V_{out} specification for various divide ratios at 1.1 GHz input frequency.

Features

- 1.1 GHz Toggle Frequency
- Supply Voltage 4.5 to 5.5 V
- Low Power 3.7 mA Typical at V_{CC} = 5.0 V
- Operating Temperature Range of −40 to 85°C
- These Devices are Pb−Free and are RoHS Compliant

Table 1. MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Power Supply Voltage, Pin 2	V_{CC}	−0.5 to 7.0	Vdc
Operating Temperature Range	T_A	−40 to 85	°C
Storage Temperature Range	T_{stg}	−65 to 150	°C
Maximum Output Current, Pin 4	I_O	10	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Table 2. ATTRIBUTES

Characteristics		Value
ESD Protection	Human Body Model Machine Model	> 1500 V > 100 V
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)		Level 1
Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test		

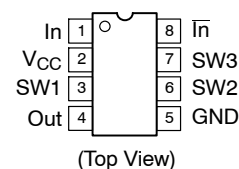1. For additional information, see Application Note AND8003/D.

ON Semiconductor®

http://onsemi.com

MARKING DIAGRAM

SOIC−8
D SUFFIX
CASE 751

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12080
ALYW
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A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
■ = Pb−Free Package

PIN CONNECTIONS

In	1	8	$\overline{In}$
V_{CC}	2	7	SW3
SW1	3	6	SW2
Out	4	5	GND

(Top View)

FUNCTION TABLE

SW1	SW2	SW3	Divide Ratio
L	L	L	80
L	L	H	40
L	H	L	40
L	H	H	20
H	L	L	40
H	L	H	20
H	H	L	20
H	H	H	10

NOTE: SW1, SW2 and SW3: H = V_{CC}, L = Open.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

Table 3. ELECTRICAL CHARACTERISTICS (V_{CC} = 4.5 to 5.5 V; T_A = −40 to 85°C, unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Toggle Frequency (Sine Wave)	ft	0.1	1.4	1.1	GHz
Supply Current Output (Pin 2)	I_{CC}	–	3.7	5.0	mA

Input Voltage Sensitivity
        100 to 250 MHz
        250 to 1100 MHz
	V_{in}	
		400
		100
			
			–
			–
				
				1000
				1000
					mVpp

Divide Ratio Control Input High (SW1, SW2, SW3)	V_{IH}	V_{CC} − 0.5 V	V_{CC}	V_{CC} + 0.5 V	V
Divide Ratio Control Input Low (SW1, SW2, SW3)	V_{IL}	Open	Open	Open	–

Output Voltage Swing (Note 1)
        R_L = 820 Ω, I_O = 4.0 mA for ÷10
        R_L = 1.6 kΩ, I_O = 2.1 mA for ÷20
        R_L = 3.3 kΩ, I_O = 1.1 mA for ÷40
        R_L = 6.2 kΩ, I_O = 0.57 mA for ÷80
	V_{out}	0.8	1.2	–	V_{pp}

1. Assumes 8.0 pF load and 1.1 GHz input frequency (typical), I_O at V_{CC} = 5.0 V and T_A = 25°C.
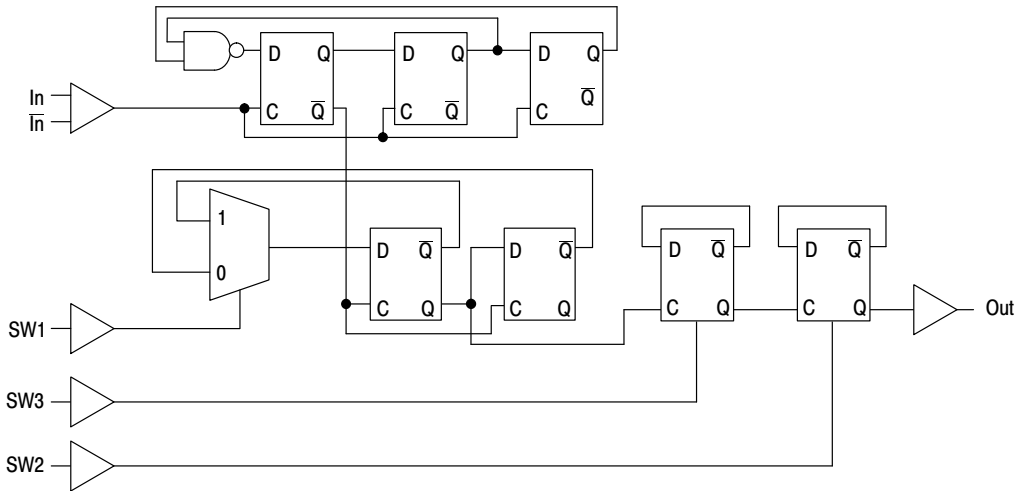
Figure 1. Logic Diagram
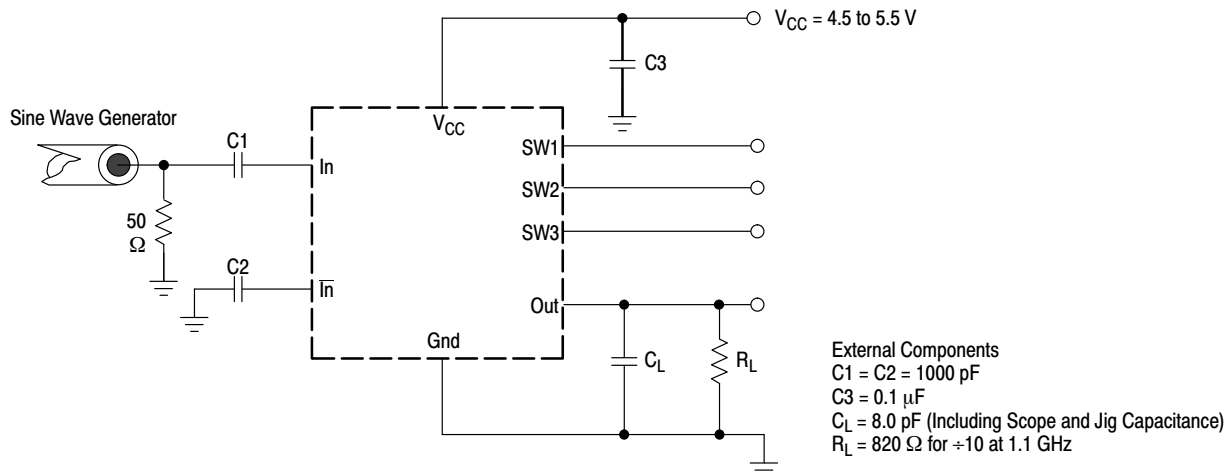
Figure 2. AC Test Circuit

MC12080

Divide Ratio = 10; V_{CC} = 5.0 V; T_A = 25°C
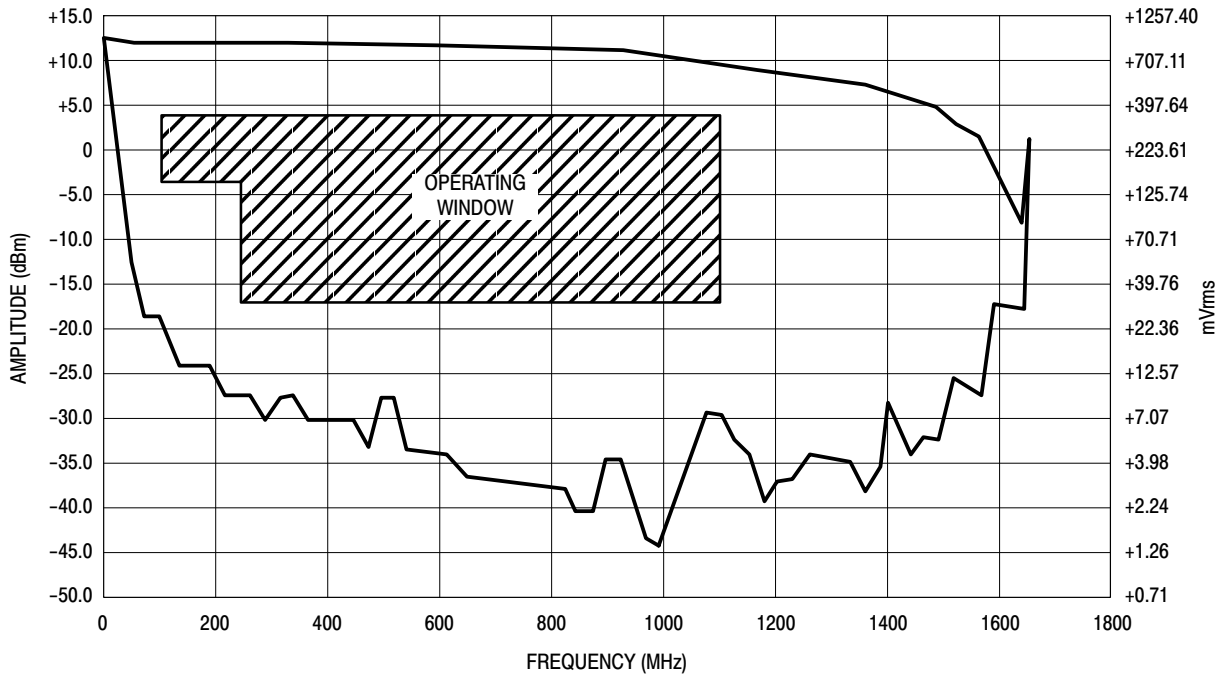
Figure 3. Input Signal Amplitude versus Input Frequency
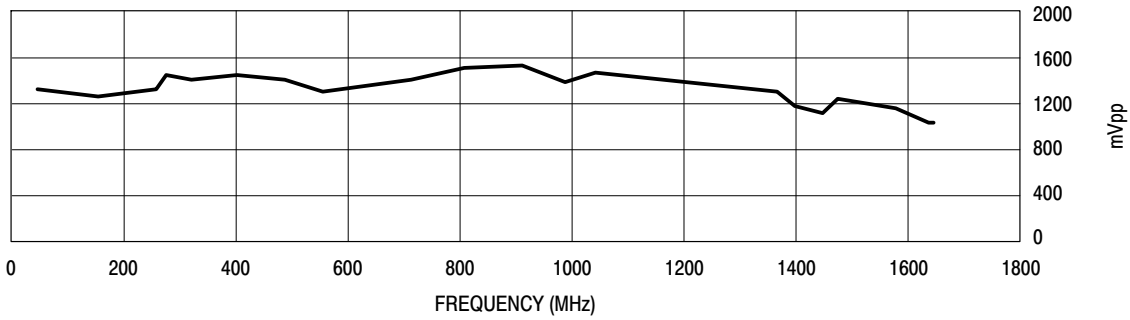
Figure 4. Output Amplitude versus Input Frequency

ORDERING INFORMATION

Device	Package	Shipping†
MC12080DG	SOIC−8 (Pb−Free)	98 Units / Rail
MC12080DR2G		2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
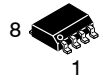
8
1
SCALE 1:1

SOIC−8 NB
CASE 751−07
ISSUE AK

DATE 16 FEB 2011
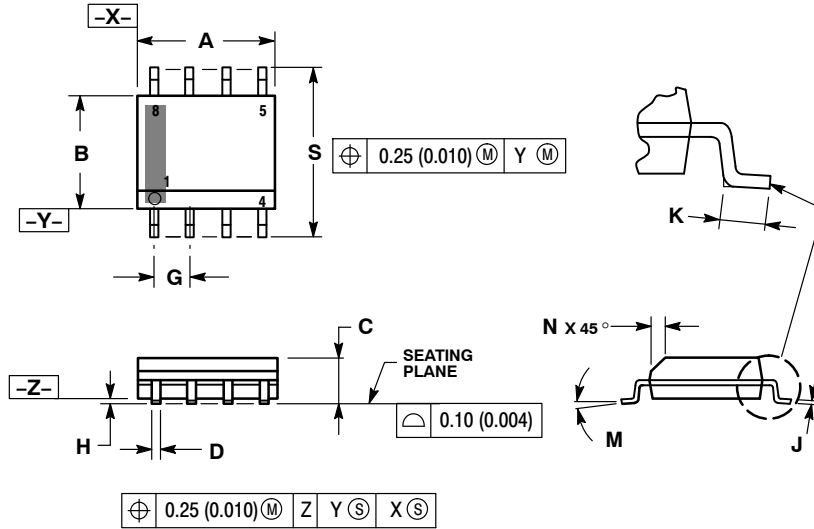
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

-X-
A
8 5
B
S
⊕ 0.25 (0.010) Ⓜ Y Ⓜ
1 4
-Y-
G

C
SEATING PLANE
-Z-
⌂ 0.10 (0.004)
H D
⊕ 0.25 (0.010)Ⓜ Z Y Ⓢ X Ⓢ

N X 45°
K
M J

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*

1.52
0.060
7.0
0.275
4.0
0.155
0.6
0.024
1.270
0.050

SCALE 6:1 (mm / inches)
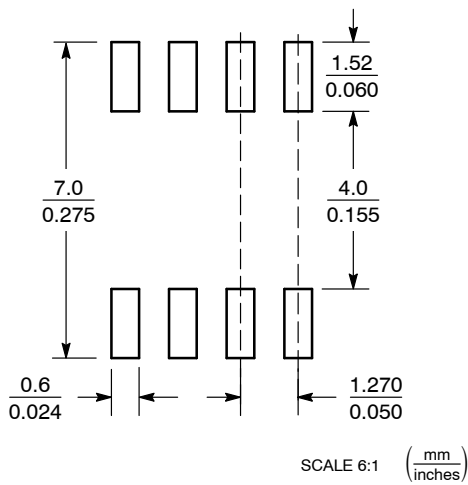
*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*
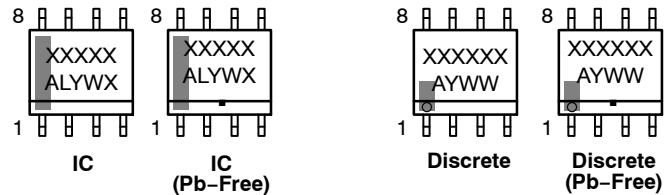
8 XXXXX ALYWX 1 — **IC**

8 XXXXX ALYWX 1 ▪ — **IC (Pb−Free)**

8 XXXXXX AYWW 1 — **Discrete**

8 XXXXXX AYWW 1 ▪ — **Discrete (Pb−Free)**

XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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DESCRIPTION:	SOIC−8 NB		PAGE 1 OF 2

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. COLLECTOR
4. EMITTER
5. EMITTER
6. BASE
7. BASE
8. EMITTER

STYLE 2:
PIN 1. COLLECTOR, DIE, #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. BASE, #2
6. EMITTER, #2
7. BASE, #1
8. EMITTER, #1

STYLE 3:
PIN 1. DRAIN, DIE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. GATE, #2
6. SOURCE, #2
7. GATE, #1
8. SOURCE, #1

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
7. ANODE
8. COMMON CATHODE

STYLE 5:
PIN 1. DRAIN
2. DRAIN
3. DRAIN
4. DRAIN
5. GATE
6. GATE
7. SOURCE
8. SOURCE

STYLE 6:
PIN 1. SOURCE
2. DRAIN
3. DRAIN
4. SOURCE
5. SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 7:
PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

STYLE 8:
PIN 1. COLLECTOR, DIE #1
2. BASE, #1
3. BASE, #2
4. COLLECTOR, #2
5. COLLECTOR, #2
6. EMITTER, #2
7. EMITTER, #1
8. COLLECTOR, #1

STYLE 9:
PIN 1. EMITTER, COMMON
2. COLLECTOR, DIE #1
3. COLLECTOR, DIE #2
4. EMITTER, COMMON
5. EMITTER, COMMON
6. BASE, DIE #2
7. BASE, DIE #1
8. EMITTER, COMMON

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT
4. GROUND
5. GROUND
6. BIAS 2
7. INPUT
8. GROUND

STYLE 11:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 12:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 14:
PIN 1. N−SOURCE
2. N−GATE
3. P−SOURCE
4. P−GATE
5. P−DRAIN
6. P−DRAIN
7. N−DRAIN
8. N−DRAIN

STYLE 15:
PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

STYLE 16:
PIN 1. EMITTER, DIE #1
2. BASE, DIE #1
3. EMITTER, DIE #2
4. BASE, DIE #2
5. COLLECTOR, DIE #2
6. COLLECTOR, DIE #2
7. COLLECTOR, DIE #1
8. COLLECTOR, DIE #1

STYLE 17:
PIN 1. VCC
2. V2OUT
3. V1OUT
4. TXE
5. RXE
6. VEE
7. GND
8. ACC

STYLE 18:
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 19:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

STYLE 20:
PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3
4. CATHODE 4
5. CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 22:
PIN 1. I/O LINE 1
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 23:
PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 24:
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

STYLE 25:
PIN 1. VIN
2. N/C
3. REXT
4. GND
5. IOUT
6. IOUT
7. IOUT
8. IOUT

STYLE 26:
PIN 1. GND
2. dv/dt
3. ENABLE
4. ILIMIT
5. SOURCE
6. SOURCE
7. SOURCE
8. VCC

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 28:
PIN 1. SW_TO_GND
2. DASIC_OFF
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBULK
7. VBULK
8. VIN

STYLE 29:
PIN 1. BASE, DIE #1
2. EMITTER, #1
3. BASE, #2
4. EMITTER, #2
5. COLLECTOR, #2
6. COLLECTOR, #2
7. COLLECTOR, #1
8. COLLECTOR, #1

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
3. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
6. SOURCE 1/DRAIN 2
7. SOURCE 1/DRAIN 2
8. GATE 1

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ADDITIONAL INFORMATION

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